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the semiconductor device further comprising a metal wire formed on the active element, the film formed of spin-on-glass in the interlayer insulating film being formed to a minimum thickness necessary for compensating the level difference of the metal wire.

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25. (Amended) A semiconductor device, comprising:

an active element provided on a semiconductor substrate;

a plurality of metal wires above said active element [in a laminated form]; and

interlayer insulating films each being provided between said metal wires,

wherein each interlayer insulating film has a multilayer structure including at least a structure in which a [film formed by the] spin-on-glass [method] film is sandwiched by insulating films each of which is either a silicon nitride film or a silicon oxide film;

the semiconductor device further comprising a metal wire formed on the active element, the film formed of spin-on-glass in the interlayer insulating film being formed to a minimum thickness necessary for compensating the level difference of the metal wire;

a pad metal for an electrode pad, said pad metal being provided on said interlayer insulating film.

REMARKS

The foregoing amendments conform to the amendments made in the parent application Serial No. 09/064,165. Claims 14 through 16, 22 and 25 are pending in this divisional application.

TOYOSAWA et al
Serial No. (to be assigned)

Examination of this application is respectfully solicited.

Respectfully submitted,

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